

μ PA2600T1R

N-CHANNEL MOSFET 20 V, 7.0 A, 13.8 m Ω

R07DS0998EJ0100 Rev.1.00 Jan 15, 2013

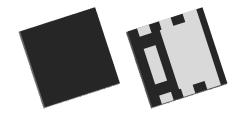
Description

The μ PA2600T1R is N-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- High Drain to Source Voltage
 - -- V_{DSS} = 20 V (V_{GS} = 0 V, T_A = 25°C)
- 2.5V drive available
- Low on-state resistance
 - $R_{DS (on)1} = 13.8 \text{ m}\Omega$ MAX. ($V_{GS} = 4.5 \text{ V}$, $I_D = 3.5 \text{ A}$)
 - $R_{DS (on)2} = 19.1 \text{ m}\Omega \text{ MAX}. (V_{GS} = 2.5 \text{ V}, I_D = 3.5 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020

Ordering Information

Part Number	Package			
μPA2600T1R-E2-AX*1	6pinHUSON2020			

Note: *1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings ($T_A = 25$ °C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V_{DSS}	20	V
Gate to Source Voltage (V _{DS} = 0 V)	V_{GSS}	±12	V
Drain Current (DC) (T _C = 25 °C)	I _{D(DC)}	±7.0	Α
Drain Current (pulse) *1	I _{D(pulse)}	±28	Α
Total Power Dissipation (5 s) *2	P _T	2.4	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes: *1. PW≤10 μs, Duty Cycle≤1%

*2. Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

Electrical Characteristics (T_A = 25°C)

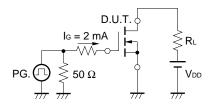
Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μA	V _{DS} = 20 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	$V_{GS(off)}$	0.5		1.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	6.5			S	$V_{DS} = 10V, I_D = 3.5 A$
Drain to Source On-state	R _{DS(on)1}		11.1	13.8	mΩ	V_{GS} = 4.5 V, I_{D} = 3.5 A
Resistance *1	R _{DS(on)2}		14.4	19.1	mΩ	$V_{GS} = 2.5 \text{ V}, I_D = 3.5 \text{ A}$
Input Capacitance	C _{iss}		870		pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output Capacitance	Coss		170		pF	f = 1.0 MHz
Reverse Transfer Capacitance	C _{rss}		110		pF	
Turn-on Delay Time	t _{d (on)}		12		ns	I_D = 3.5 A, V_{DD} = 10 V, V_{GS} = 4 V, R_G = 6 Ω
Rise Time	t _r		10		ns	
Turn-off Delay Time	t _{d (off)}		42		ns	
Fall Time	t _f		9		ns	
Total Gate Charge	Q_G		7.9		nC	I _D = 7.0 A , V _{DD} = 16 V,
Gate to Source Charge	Q _{GS}		1.7		nC	V _{GS} = 10 V
Gate to Drain Charge	Q_{GD}		2.8		nC	
Body Diode Forward Voltage *1	$V_{F(S-D)}$			1.5	V	I _F = 7.0 A, V _{GS} = 0 V

Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME

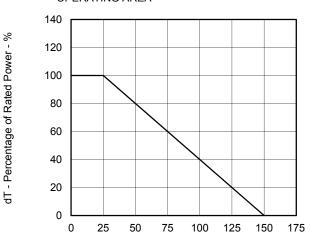
PG. \bigcirc Relative Form V_{GS} V_{DS} V_{DS}

TEST CIRCUIT 2 GATE CHARGE



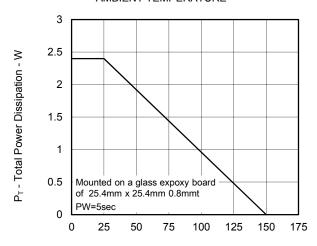
Typical Characteristics $(T_A = 25^{\circ}C)$

DERATING FACTOR OF FORWARD BIAS SAFE **OPERATING AREA**



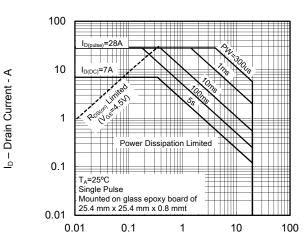
T_A -Ambient Temperature - °C

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



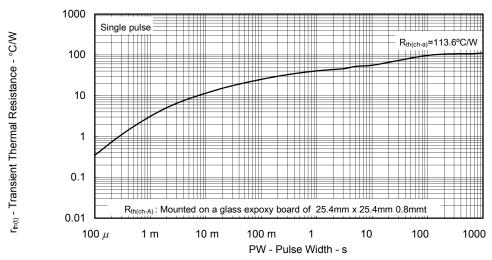
T_A -Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



V_{DS} - Drain to Source Voltage - V

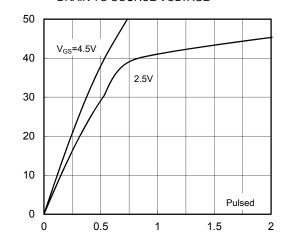
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



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I_D -Drain Current - A

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE

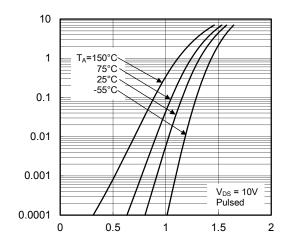


V_{DS} - Drain to Source Voltage - V

I_D - Drain Current - A

| y_{fs} | - Forward Transfer Admittance - S

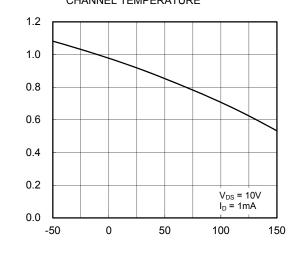
R_{DS(on)} – Drain to Source On-state Resistance - mΩ



FORWARD TRANSFER CHARACTERISTICS

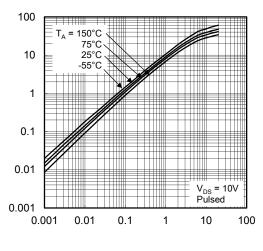
V_{GS} - Gate to Source Voltage - V

GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



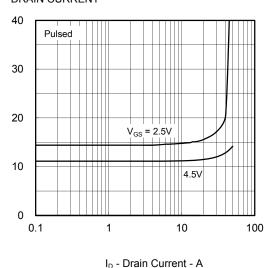
 T_{ch} - Channel Temperature - $^{\circ}\text{C}$

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

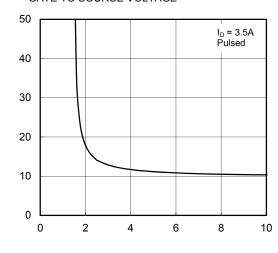


I_D – Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



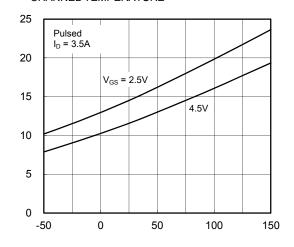
V_{GS} - Gate to Source Voltage - V

V_{GS(off)} – Gate to Source Cut-off Voltage - V

R_{DS(on)} –Drain to Source On-state Resistance - mΩ

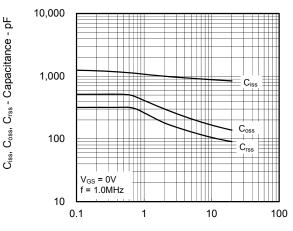
t_{d(on)}, t_f, t_{d(off)}, t_r - Switching Time -ns

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



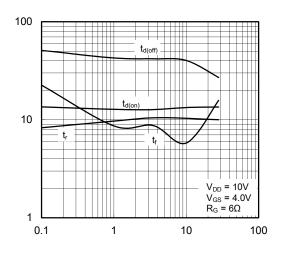
T_{ch} - Channel Temperature - °C

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



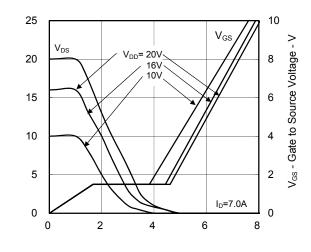
V_{DS} - Drain to Source Voltage - V

SWITCHING CHARACTERISTICS



ID - Drain Current - A

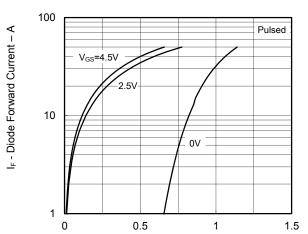
DYNAMIC INPUT/OUTPUT CHARACTERISTICS



V_{DS} - Drain to Source Voltage - V

 $\ensuremath{\mathsf{Q}}_G$ - Gate Charge - nC

SOURCE TO DRAIN DIODE FORWARD VOLTAGE

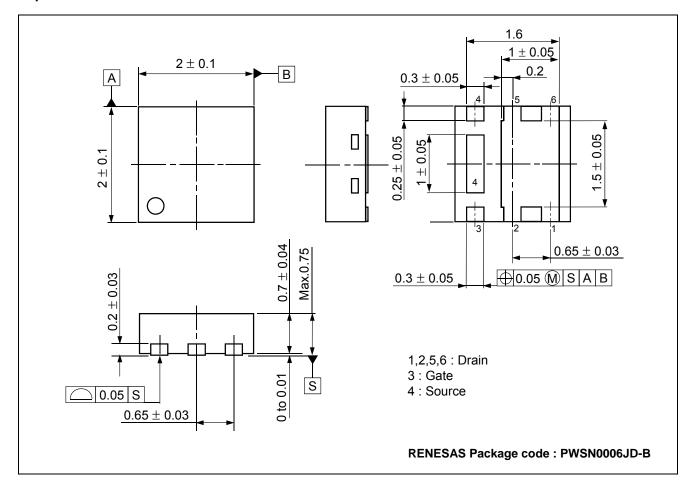


 $V_{F(S\!-\!D)}$ - Drain to Source Voltage - V

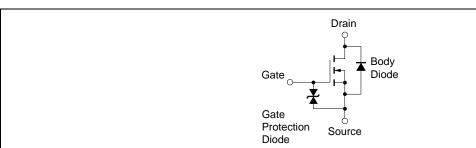
Free Datasheet http://www.datasheet4u.com/

Package Drawings (Unit: mm)

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Equivalent Circuit



Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

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